



DATA SHEET

SEMICONDUCTOR

RB751G-40

Schottky barrier diode



●Applications

General rectification

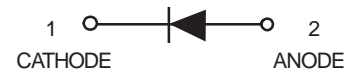
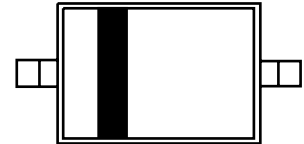
●Features

- 1) Small power mold type.
(SOD-723)
- 2) Low V_F
- 3) High reliability
- 4) Pb-Free package is available

●Construction

Silicon epitaxial planar

SOD-723



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	40	V
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_o	30	mA
Forward current surge peak (60Hz·1cyc)	I_{FSM}	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

●Electrical characteristic (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.37	V	$I_F=1mA$
Reverse current	I_R	-	-	0.5	μA	$V_R=30V$
Capacitance between terminals	C_t	-	2	-	pF	$V_R=1V, f=1MHz$

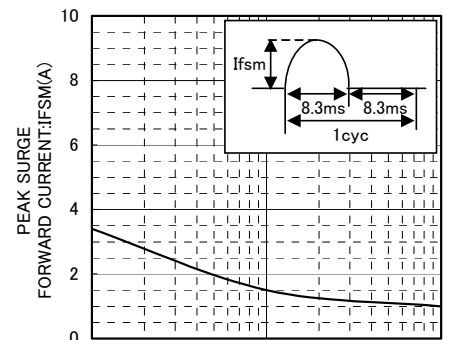
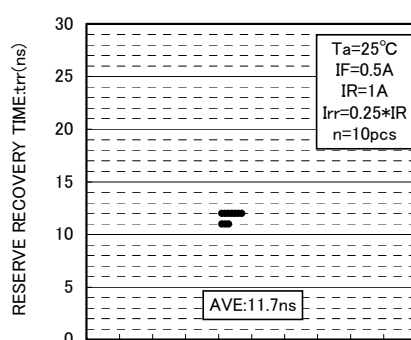
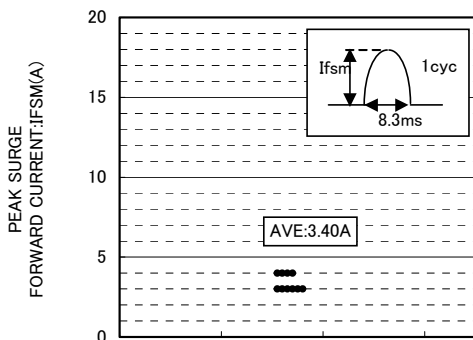
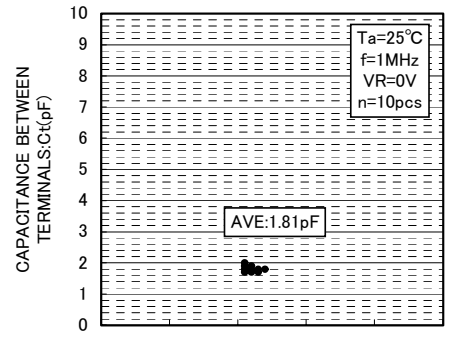
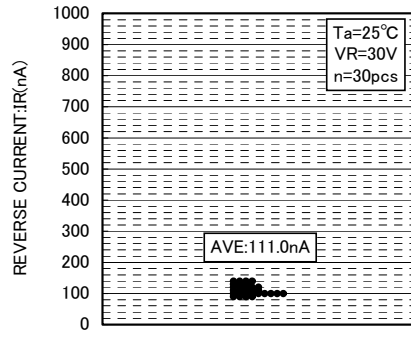
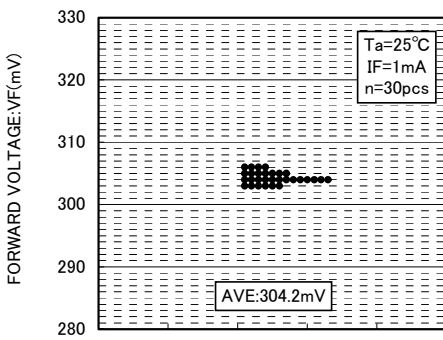
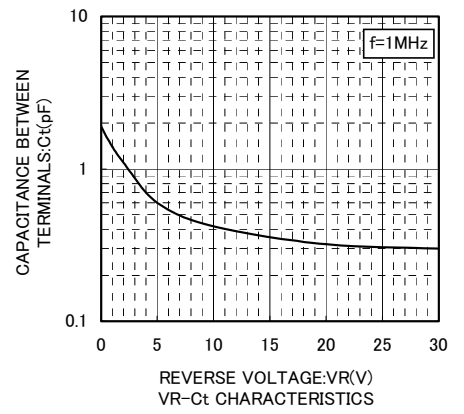
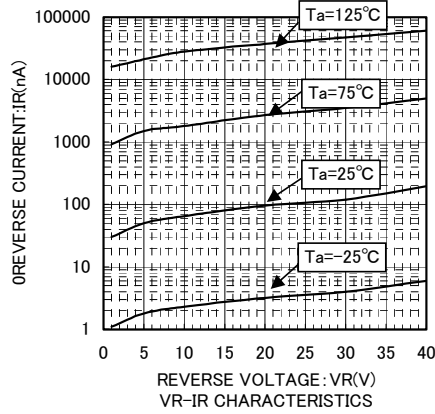
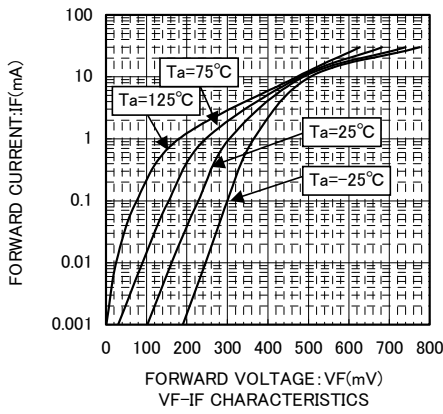
●DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
RB751G-40	5	3000/Tape&Reel

DEVICE CHARACTERISTICS

RB751G-40

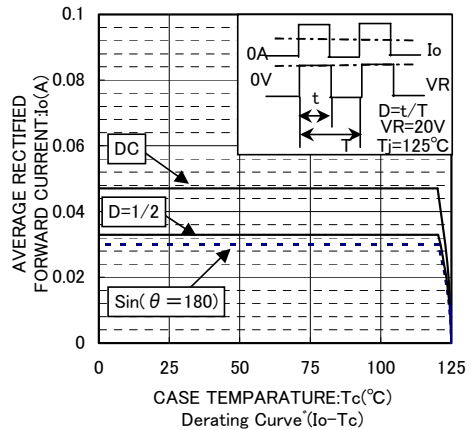
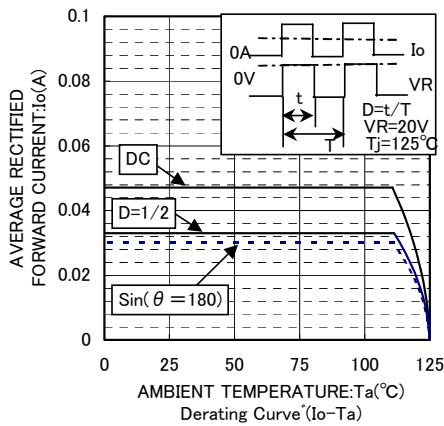
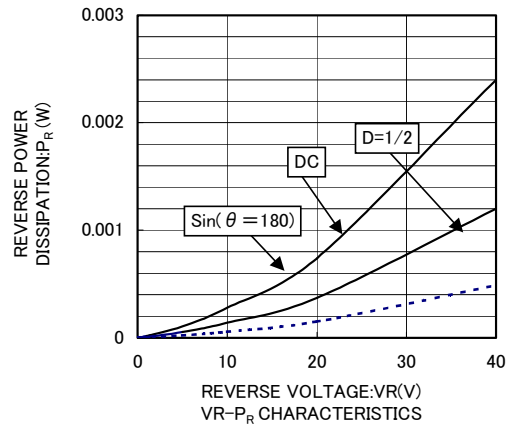
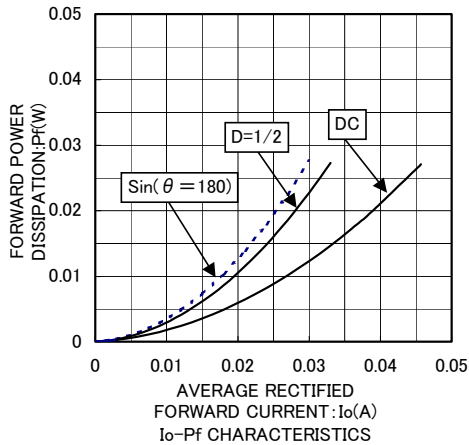
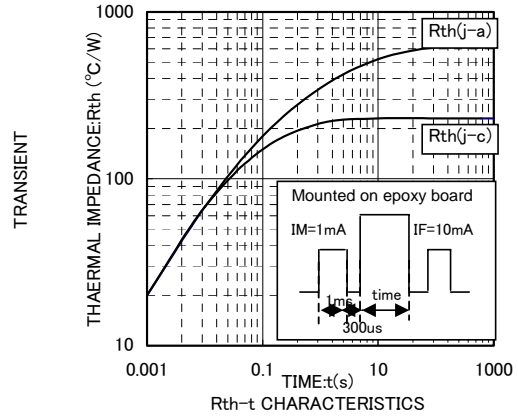
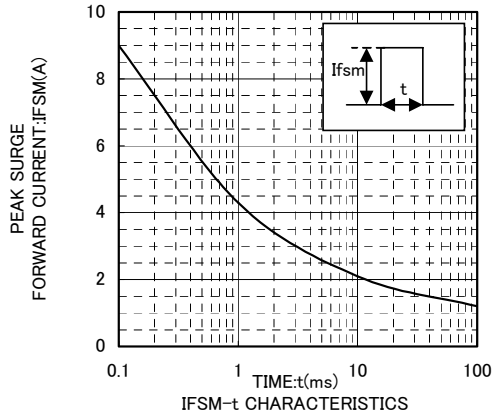
Electrical characteristic curves (Ta=25°C)



DEVICE CHARACTERISTICS

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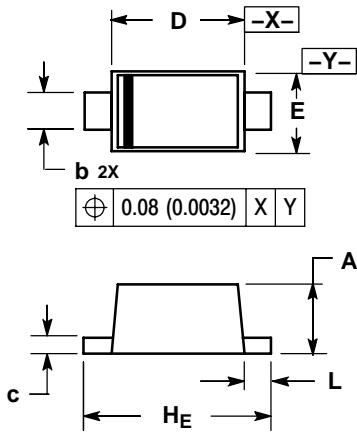
Electrical characteristic curves ($T_a=25^\circ\text{C}$)



PACKAGE OUTLINE & DIMENSIONS

RB751G-40

SOD-723



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.49	0.52	0.55	0.019	0.020	0.022
b	0.25	0.28	0.32	0.0098	0.011	0.013
c	0.08	0.12	0.15	0.0032	0.0047	0.0059
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	1.35	1.40	1.45	0.053	0.055	0.057
L	0.15	0.20	0.25	0.006	0.0079	0.010

SOLDERING FOOTPRINT*

